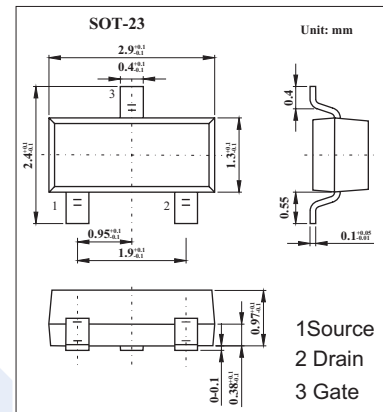


N-Channel Junction Silicon FET

2SK303

■ Features

- Ideal for potentiometers, analog switches, low frequency amplifiers, constant current supplies, and impedance conversion.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	30	V
Gate to Drain voltage	V_{GDS}	-30	V
Gate current	I_G	10	m A
Drain current	I_D	20	m A
Power dissipation	P_D	200	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

* $PW \leq 10 \mu s$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Gate to drain	V_{GDS}	$I_G = -10 \mu A$	-30			V
Gate to source leakage current	I_{GSS}	$V_{GS} = -20V$			-1.0	nA
Drain cut-off current	I_{DSS}	$V_{DS} = 10V, V_{GS} = 0$	0.6		12.0	mA
Cutoff voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 1 \mu A$		-1	-4	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	2.5	6.0		ms
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS} = 0, V_{DS} = 10mV$		250		Ω
Input capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		5		pF
Reverse transfer capacitance	C_{rss}			1.5		pF

■ I_{DSS} Classification unit: mA

Marking	V2	V3	V4	V5
Rank	2	3	4	5
I_{DSS}	0.6~1.5	1.2~3.0	2.5~6.0	5.0~12.0